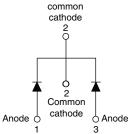


Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 2 x 8 A







PRODUCT SUMMARY						
Package	TO-220AB					
I _{F(AV)}	2 x 8 A					
V _R	600 V					
V _F at I _F	1.4 V					
t _{rr} typ.	18 ns					
T _J max.	150 °C					
Diode variation	Common cathode					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to JEDEC[®]-JESD47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA16TA60C... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A per leg continuous current, the VS-HFA16TA60C... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TA60C... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Cathode to anode voltage	V _R		600	V				
Maximum continuous forward current	I_	T _C = 100 °C	8					
per device	I _F	1C = 100 C	16	А				
Single pulse forward current	I _{FSM}		60	~				
Maximum repetitive forward current	I _{FRM}		24					
Maximum power dissipation	р	T _C = 25 °C	36	W				
Maximum power dissipation	P _D	T _C = 100 °C	14	vv				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C				

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1

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RoHS

COMPLIANT

HALOGEN

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ELECTRICAL SPECIFICATIONS PER LEG ($T_J = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-		
		I _F = 8 A		-	1.4	1.7	V	
Maximum forward voltage	V _{FM}	I _F = 16 A	See fig. 1	-	1.7	2.1		
		$I_F = 8 \text{ A}, \text{T}_\text{J} = 125 \ ^\circ\text{C}$		-	1.4	1.7		
Maximum reverse		$V_{R} = V_{R}$ rated	See fig. 0	-	0.3	5.0		
leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated	See fig. 2	-	100	500	μA	
Junction capacitance	CT	V _R = 200 V See fig. 3		-	10	25	pF	
Series inductance	L _S	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH	

DYNAMIC RECOVERY CHARACTERISTICS PER LEG ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS				UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	A/μs, V _R = 30 V	-	18	-		
Reverse recovery time See fig. 5 and 10	t _{rr1}	T _J = 25 °C		-	37	55	ns	
	t _{rr2}	T _J = 125 °C		-	55	90		
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 8.0 A	-	3.5	5.0	A	
See fig. 6	I _{RRM2}	T _J = 125 °C		-	4.5	8.0		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	$dI_F/dt = 200 A/\mu s$	-	65	138	nC	
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	124	360		
Peak rate of fall recovery current during t _b	dl _{(rec)M} /dt1	T _J = 25 °C		-	240	-	A∕µs	
See fig. 8	dl _{(rec)M} /dt2	T _J = 125 °C		-	210	-	7γμ3	

THERMAL - MECHANICAL SPECIFICATIONS PER LEG							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Junction to case, single leg conducting	1		-	-	3.5		
Junction to case, both legs conducting	R _{thJC}		-	-	1.75	к/W	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	10,10	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-		
Weight			-	2.0	-	g	
weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-220AB		HFA16	TA60C		

Revision: 14-Jul-15



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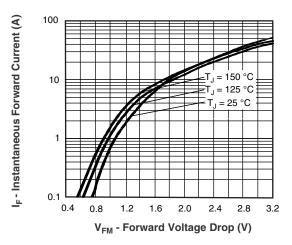
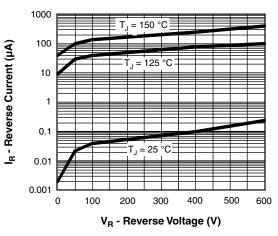
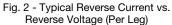
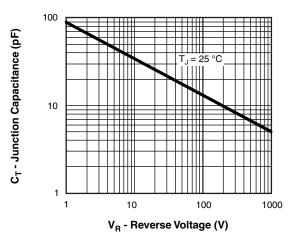


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)









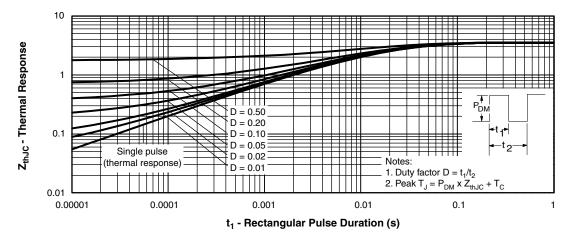


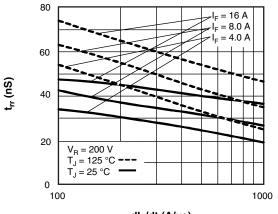
Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

 Revision: 14-Jul-15
 3
 Document Number: 94058

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dl_F/dt (A/µs)



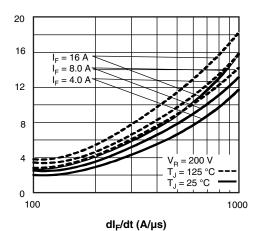
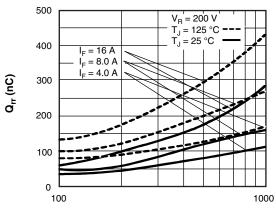
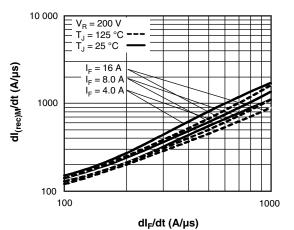


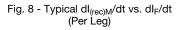
Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)



dl_F/dt (A/µs)

Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)





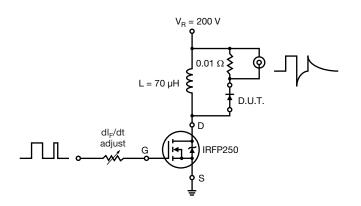


Fig. 9 - Reverse Recovery Parameter Test Circuit

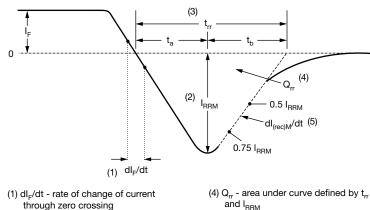
 Revision: 14-Jul-15
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I_{rr} (A)



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(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RBM} and 0.50 I_{RBM} extrapolated to zero current. and I_{RRM}

$$Q_{\rm rr} = \frac{l_{\rm rr} \times l_{\rm RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	16	ТА	60	С	PbF
		2	3	4	5	6	(7)	8
	1 -	Visł	nay Sem	niconduc	tors pro	oduct		
	2 -	HEX	(FRED	[®] family				
	3 -	Eleo	ctron irra	adiated				
	4 -	Cur	rent rati	ng (16 =	16 A)			
	5 -	Pac	kage:					
		TA	= TO-22	20AB				
	6 -	Volt	age rati	ng (60 =	= 600 V)			
	7 -			iguratior on catho				
	8 -	Env	ironmer	ntal digit	:			
		PbF	= lead	(Pb)-fre	e and R	oHS-co	mpliant	t
		-N3	= halog	en-free,	RoHS-	complia	nt, and	totally l

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-HFA16TA60CPbF	50	1000	Antistatic plastic tube					
VS-HFA16TA60C-N3	50	1000	Antistatic plastic tube					

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95222						
Deut verend immediate	TO-220ABPbF	www.vishay.com/doc?95225				
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028				

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TO-220AB

DIMENSIONS in millimeters and inches





.ead	assignments

Diodes

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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